

# Enrico Napolitani

## List of Publications by Year in descending order

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214  
papers

3,481  
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147801

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47  
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216  
all docs

216  
docs citations

216  
times ranked

2248  
citing authors

#	ARTICLE	IF	CITATIONS
1	Cerium-based chemical conversion coating on AZ63 magnesium alloy. Surface and Coatings Technology, 2003, 172, 227-232.	4.8	216
2	Mechanisms of boron diffusion in silicon and germanium. Journal of Applied Physics, 2013, 113, .	2.5	95
3	Strain relaxation in graded composition $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ buffer layers. Journal of Applied Physics, 1999, 86, 4748-4755.	2.5	89
4	Interaction between self-interstitials and substitutional C in silicon: Interstitial trapping and C clustering mechanism. Physical Review B, 2002, 65, .	3.2	89
5	Tunability of the dielectric function of heavily doped germanium thin films for mid-infrared plasmonics. Physical Review B, 2016, 94, .	3.2	86
6	Lattice parameter of $\text{Si}_{1-x}\text{Ge}_x$ alloys. Physical Review B, 2000, 61, 13005-13013.	3.2	78
7	Fluorine effect on As diffusion in Ge. Journal of Applied Physics, 2011, 109, .	2.5	73
8	Flash lamp annealing with millisecond pulses for ultra-shallow boron profiles in silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 287-291.	1.4	61
9	Dissolution kinetics of boron-interstitial clusters in silicon. Applied Physics Letters, 2003, 83, 680-682.	3.3	61
10	N-type doping of Ge by As implantation and excimer laser annealing. Journal of Applied Physics, 2014, 115, .	2.5	57
11	Fluorine in Si: Native-defect complexes and the suppression of impurity diffusion. Physical Review B, 2005, 72, .	3.2	53
12	Underground study of the $\text{O}_2$ reaction relevant for explosive hydrogen burning. Physical Review C, 2014, 89, .	2.9	53
13	Role of fluorine in suppressing boron transient enhanced diffusion in preamorphized Si. Applied Physics Letters, 2004, 84, 1862-1864.	3.3	52
14	First Direct Measurement of the $\text{O}_2$ reaction relevant for explosive hydrogen burning. Physical Review C, 2014, 89, .	3.3	52
15	Complete suppression of the transient enhanced diffusion of B implanted in preamorphized Si by interstitial trapping in a spatially separated C-rich layer. Applied Physics Letters, 2001, 79, 4145-4147.	3.3	46
16	Ga-implantation in Ge: Electrical activation and clustering. Journal of Applied Physics, 2009, 106, .	2.5	45
17	Mechanism of Boron Diffusion in Amorphous Silicon. Physical Review Letters, 2008, 100, 155901.	7.8	44
18	Preparation and characterisation of isotopically enriched Ta <sub>2</sub> O <sub>5</sub> targets for nuclear astrophysics studies. European Physical Journal A, 2012, 48, 1.	2.5	43

#	ARTICLE	IF	CITATIONS
19	Electrical behavior of ultra-low energy implanted boron in silicon. Journal of Applied Physics, 2000, 88, 1299-1306.	2.5	42
20	Quantitative carrier profiling in ion-implanted 6H-SiC. Applied Physics Letters, 2001, 79, 1211-1213.	3.3	42
21	Formation and dissolution of D-N complexes in dilute nitrides. Physical Review B, 2007, 76, .	3.2	42
22	Microscopical aspects of boron diffusion in ultralow energy implanted silicon. Applied Physics Letters, 1999, 75, 1869-1871.	3.3	40
23	Mechanism of B diffusion in crystalline Ge under proton irradiation. Physical Review B, 2009, 80, .	3.2	39
24	Hydrogen-nitrogen complexes in dilute nitride alloys: Origin of the compressive lattice strain. Applied Physics Letters, 2006, 89, 061904.	3.3	38
25	Evolution of boron-interstitial clusters in crystalline Si studied by transmission electron microscopy. Applied Physics Letters, 2007, 91, 031905.	3.3	37
26	B-doping in Ge by excimer laser annealing. Journal of Applied Physics, 2013, 113, .	2.5	37
27	Resonance strengths in the $^{17,18}\text{O}(p, \hat{\pm})^{14,15}\text{N}$ reactions and background suppression underground. European Physical Journal A, 2015, 51, 1.	2.5	37
28	Surface properties of AZ91 magnesium alloy after PEO treatment using molybdate salts and low current densities. Applied Surface Science, 2015, 357, 1031-1039.	6.1	35
29	C ion-implanted TiO <sub>2</sub> thin film for photocatalytic applications. Journal of Applied Physics, 2015, 117, .	2.5	35
30	Extended Point Defects in Crystalline Materials: Ge and Si. Physical Review Letters, 2013, 110, 155501.	7.8	34
31	Thermodynamic stability of high phosphorus concentration in silicon nanostructures. Nanoscale, 2015, 7, 14469-14475.	5.6	33
32	Oxidation rate enhancement of SiGe epitaxial films oxidized in dry ambient. Applied Physics Letters, 2003, 83, 3713-3715.	3.3	31
33	Fluorine in preamorphized Si: Point defect engineering and control of dopant diffusion. Journal of Applied Physics, 2006, 99, 103510.	2.5	31
34	Transient enhanced diffusion of B mediated by self-interstitials in preamorphized Ge. Applied Physics Letters, 2010, 96, .	3.3	31
35	Room Temperature Migration of Boron in Crystalline Silicon. Physical Review Letters, 2004, 93, 055901.	7.8	30
36	Fluorine segregation and incorporation during solid-phase epitaxy of Si. Applied Physics Letters, 2005, 86, 121905.	3.3	30

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37	Underground nuclear astrophysics: Why and how. <i>European Physical Journal A</i> , 2016, 52, 1.	2.5	30
38	Depth distribution of B implanted in Si after excimer laser irradiation. <i>Applied Physics Letters</i> , 2005, 86, 051909.	3.3	29
39	Effects of helium ion bombardment on metallic gold and iridium thin films. <i>Optical Materials Express</i> , 2015, 5, 176.	3.0	29
40	Atomistic Mechanism of Boron Diffusion in Silicon. <i>Physical Review Letters</i> , 2006, 97, 255902.	7.8	28
41	Optical properties of highly n-doped germanium obtained by <i>in situ</i> doping and laser annealing. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 465103.	2.8	28
42	Phase field model of the nanoscale evolution during the explosive crystallization phenomenon. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	28
43	Atomic transport properties and electrical activation of ultra-low energy implanted boron in crystalline silicon. <i>Materials Science in Semiconductor Processing</i> , 1999, 2, 35-44.	4.0	27
44	Synthesis and characterization of P $\delta$ -layer in SiO <sub>2</sub> by monolayer doping. <i>Nanotechnology</i> , 2016, 27, 075606.	2.6	27
45	Low temperature deactivation of Ge heavily n-type doped by ion implantation and laser thermal annealing. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	27
46	Quantification of phosphorus diffusion and incorporation in silicon nanocrystals embedded in silicon oxide. <i>Surface and Interface Analysis</i> , 2014, 46, 393-396.	1.8	26
47	Experimental evidences for two paths in the dissolution process of B clusters in crystalline Si. <i>Applied Physics Letters</i> , 2005, 87, 221902.	3.3	25
48	Laser annealing in Si and Ge: Anomalous physical aspects and modeling approaches. <i>Materials Science in Semiconductor Processing</i> , 2017, 62, 80-91.	4.0	25
49	An investigation on the modeling of transient enhanced diffusion of ultralow energy implanted boron in silicon. <i>Journal of Applied Physics</i> , 2001, 89, 5381-5385.	2.5	23
50	Mesoscopic-capacitor effect in GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N quantum wells: Effects on the electronic states. <i>Physical Review B</i> , 2001, 63, .	3.2	22
51	High-resolution X-ray diffraction <i>in situ</i> study of very small complexes: the case of hydrogenated dilute nitrides. <i>Journal of Applied Crystallography</i> , 2008, 41, 366-372.	4.5	22
52	Anomalous transport of Sb in laser irradiated Ge. <i>Applied Physics Letters</i> , 2012, 101, 172110.	3.3	22
53	Evidences of F-induced nanobubbles as sink for self-interstitials in Si. <i>Applied Physics Letters</i> , 2006, 89, 171916.	3.3	21
54	Lattice curvature generation in graded In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs buffer layers. <i>Physical Review B</i> , 2000, 62, 11054-11062.	3.2	20

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55	Carrier concentration and mobility in B doped Si <sub>1-x</sub> Ge <sub>x</sub> . Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 49-52.	3.5	20
56	Detailed arsenic concentration profiles at Si/SiO <sub>2</sub> interfaces. Journal of Applied Physics, 2008, 104, 043507.	2.5	20
57	Role of surface and of dopant-impurity interactions on the electrical activation of B implants in crystalline Si. Applied Physics Letters, 1998, 72, 3011-3013.	3.3	19
58	Clustering of ultra-low-energy implanted boron in silicon during postimplantation annealing. Applied Physics Letters, 1999, 74, 3996-3998.	3.3	19
59	Silicon interstitial injection during dry oxidation of SiGe/Si layers. Journal of Applied Physics, 2005, 97, 036106.	2.5	19
60	Experimental evidence of B clustering in amorphous Si during ultrashallow junction formation. Applied Physics Letters, 2006, 89, 241901.	3.3	19
61	N-type heavy doping with ultralow resistivity in Ge by Sb deposition and pulsed laser melting. Applied Surface Science, 2020, 509, 145229.	6.1	19
62	Formation and evolution of F nanobubbles in amorphous and crystalline Si. Applied Physics Letters, 2008, 93, 061906.	3.3	18
63	Optimal process parameters for phosphorus spin-on-doping of germanium. Applied Surface Science, 2017, 392, 1173-1180.	6.1	18
64	Carrier distribution in quantum nanostructures by scanning capacitance microscopy. Journal of Applied Physics, 2005, 97, 014302.	2.5	17
65	Role of surface nanovoids on interstitial trapping in He implanted crystalline Si. Applied Physics Letters, 2006, 88, 191910.	3.3	17
66	Lattice strain induced by boron clusters in crystalline silicon. Semiconductor Science and Technology, 2006, 21, L41-L44.	2.0	17
67	Morphological and Functional Modifications of Optical Thin Films for Space Applications Irradiated with Low-Energy Helium Ions. ACS Applied Materials & Interfaces, 2018, 10, 34781-34791.	8.0	17
68	He induced nanovoids for point-defect engineering in B-implanted crystalline Si. Journal of Applied Physics, 2007, 101, 023515.	2.5	16
69	Aluminium Implantation in Germanium: Uphill Diffusion, Electrical Activation, and Trapping. Applied Physics Express, 2012, 5, 021301.	2.4	16
70	Fluorine in Ge: Segregation and EOR-defects stabilization. Nuclear Instruments & Methods in Physics Research B, 2012, 282, 21-24.	1.4	16
71	A critical evaluation of Ag- and Ti-hyperdoped Si for Si-based infrared light detection. Journal of Applied Physics, 2021, 129, .	2.5	16
72	Vacancy effects in transient diffusion of Sb induced by ion implantation of Si <sup>+</sup> and As <sup>+</sup> ions. Journal of Applied Physics, 2000, 87, 8461-8466.	2.5	15

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73	Matrix effects in SIMS depth profiles of SiGe relaxed buffer layers. Applied Surface Science, 2004, 231-232, 704-707.	6.1	15
74	Fluorine counter doping effect in B-doped Si. Applied Physics Letters, 2007, 91, 132101.	3.3	15
75	Impurity and defect interactions during laser thermal annealing in Ge. Journal of Applied Physics, 2016, 119, .	2.5	15
76	Boron diffusion in extrinsically doped crystalline silicon. Physical Review B, 2010, 81, .	3.2	14
77	Monolayer doping of germanium by phosphorus-containing molecules. Nanotechnology, 2018, 29, 465702.	2.6	14
78	Fabrication of ultra-shallow junctions with high electrical activation by excimer laser annealing. Materials Science in Semiconductor Processing, 2001, 4, 417-423.	4.0	13
79	Electrical activation of ultralow energy As implants in Si. Journal of Applied Physics, 2001, 90, 3873-3878.	2.5	13
80	Effect of Strain on the Carrier Mobility in Heavily Dopedp-Type Si. Physical Review Letters, 2006, 97, 136605.	7.8	13
81	Substitutional B in Si: Accurate lattice parameter determination. Journal of Applied Physics, 2007, 101, 093523.	2.5	13
82	B clustering in amorphous Si. Journal of Vacuum Science & Technology B, 2008, 26, 382.	1.3	13
83	Role of oxygen on the electrical activation of B in Ge by excimer laser annealing. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 122-125.	1.8	13
84	Electrical compensation via vacancyâ€“donor complexes in arsenic-implanted and laser-annealed germanium. Applied Physics Letters, 2016, 109, .	3.3	13
85	Self-limiting Sb monolayer as a diffusion source for Ge doping. Applied Surface Science, 2019, 496, 143713.	6.1	13
86	Role of F on the Electrical Activation of As in Ge. ECS Journal of Solid State Science and Technology, 2012, 1, Q44-Q46.	1.8	12
87	Oxygen behavior in germanium during melting laser thermal annealing. Materials Science in Semiconductor Processing, 2016, 42, 196-199.	4.0	12
88	High level active <i>n</i>+ doping of strained germanium through co-implantation and nanosecond pulsed laser melting. Journal of Applied Physics, 2018, 123, .	2.5	12
89	Charge storage and screening of the internal field in GaN/AlGaIn quantum wells. Journal of Crystal Growth, 2001, 230, 492-496.	1.5	11
90	Dry oxidation of MBE-SiGe films: rate enhancement, Ge redistribution and defect injection. Materials Science in Semiconductor Processing, 2005, 8, 219-224.	4.0	11

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91	Strain engineered segregation regimes for the fabrication of thin Si $_{1-x}$ Ge $_x$ layers with abrupt n-type doping. Journal of Applied Physics, 2010, 107, .	2.5	11
92	Fluorine redistribution and incorporation during solid phase epitaxy of preamorphized Si. Physical Review B, 2010, 82, .	3.2	11
93	Self-Interstitials Injection in crystalline Ge induced by GeO $_2$ nanoclusters. Physical Review B, 2011, 84, .	3.2	11
94	Defect complexes in fluorine-implanted germanium. Journal Physics D: Applied Physics, 2013, 46, 505310.	2.8	11
95	Characterization and modeling of thermally-induced doping contaminants in high-purity germanium. Journal Physics D: Applied Physics, 2019, 52, 035104.	2.8	11
96	Transient-enhanced diffusion of boron implanted at ultralow energies in silicon: Localization of the source. Applied Physics Letters, 2000, 76, 3058-3060.	3.3	10
97	Ultrashallow profiling of semiconductors by secondary ion mass spectrometry:. Materials Science in Semiconductor Processing, 2001, 4, 55-60.	4.0	10
98	Direct observation of two-dimensional diffusion of the self-interstitials in crystalline Si. Physical Review B, 2002, 66, .	3.2	10
99	Room temperature migration of boron in crystalline silicon during secondary ion mass spectrometry profiling. Journal of Vacuum Science & Technology B, 2006, 24, 394.	1.3	10
100	He implantation in Si for B diffusion control. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 181-185.	1.4	10
101	Formation and incorporation of SiF $_4$ molecules in F-implanted preamorphized Si. Applied Physics Letters, 2009, 95, 101908.	3.3	10
102	Role of self-interstitials on B diffusion in Ge. Nuclear Instruments & Methods in Physics Research B, 2012, 282, 8-11.	1.4	10
103	Study of carrier concentration profiles in Al-implanted Ge by micro-Raman spectroscopy under different excitation wavelengths. Journal of Raman Spectroscopy, 2013, 44, 665-669.	2.5	10
104	Modeling of phosphorus diffusion in silicon oxide and incorporation in silicon nanocrystals. Journal of Materials Chemistry C, 2016, 4, 3531-3539.	5.5	10
105	In situ ohmic contact formation for n-type Ge via non-equilibrium processing. Semiconductor Science and Technology, 2017, 32, 115006.	2.0	10
106	Nanoscale measurements of phosphorous-induced lattice expansion in nanosecond laser annealed germanium. APL Materials, 2018, 6, 058504.	5.1	10
107	Pulsed laser diffusion of thin hole-barrier contacts in high purity germanium for gamma radiation detectors. European Physical Journal A, 2018, 54, 1.	2.5	10
108	Gold-Hyperdoped Germanium with Room-Temperature Sub-Band-Gap Optoelectronic Response. Physical Review Applied, 2020, 14, .	3.8	10

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109	Depth profiling of ultrashallow B implants in silicon using a magnetic-sector secondary ion mass spectrometry instrument. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 519.	1.6	9
110	Effect of Oxygen on the Diffusion of Nitrogen Implanted in Silicon. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G161.	2.2	9
111	The effect of surface treatment with atmospheric pressure plasma jet, generated by air, on corrosion properties of AISI 304L stainless steel. <i>Materials Chemistry and Physics</i> , 2012, 136, 1073-1080.	4.0	9
112	Effects of atmospheric pressure plasma JET treatment on aluminium alloys. <i>Surface Engineering</i> , 2014, 30, 636-642.	2.2	9
113	Liquid-Phase Monolayer Doping of InGaAs with Si-, S-, and Sn-Containing Organic Molecular Layers. <i>ACS Omega</i> , 2017, 2, 1750-1759.	3.5	9
114	Zn <sub>0.85</sub> Cd <sub>0.15</sub> Se active layers on graded-composition In <sub>x</sub> Ga <sub>1-x</sub> As buffer layers. <i>Journal of Applied Physics</i> , 1999, 85, 8160-8169.	2.5	8
115	Diffusion enhanced carbon loss from SiGeC layers due to oxidation. <i>Physical Review B</i> , 2001, 64, .	3.2	8
116	Investigation of germanium implanted with aluminum by multi-laser micro-Raman spectroscopy. <i>Thin Solid Films</i> , 2013, 541, 76-78.	1.8	8
117	Ion Implantation Defects and Shallow Junctions in Si and Ge. <i>Semiconductors and Semimetals</i> , 2015, 91, 93-122.	0.7	8
118	Diffusion doping of germanium by sputtered antimony sources. <i>Materials Science in Semiconductor Processing</i> , 2018, 75, 118-123.	4.0	8
119	Electronic band structures of undoped and P-doped Si nanocrystals embedded in SiO <sub>2</sub> . <i>Journal of Materials Chemistry C</i> , 2018, 6, 119-126.	5.5	8
120	Cell formation in stanogermanides using pulsed laser thermal anneal on Ge <sub>0.91</sub> Sn <sub>0.09</sub> . <i>Materials Science in Semiconductor Processing</i> , 2021, 121, 105399.	4.0	8
121	Structural characterization and modeling of damage accumulation in In implanted Si. <i>Journal of Applied Physics</i> , 2004, 95, 150-155.	2.5	7
122	Diffusion of ion beam injected self-interstitial defects in silicon layers grown by molecular beam epitaxy. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2004, 216, 286-290.	1.4	7
123	B activation enhancement in submicron confined implants in Si. <i>Applied Physics Letters</i> , 2005, 87, 133110.	3.3	7
124	B diffusion and activation phenomena during post-annealing of C co-implanted ultra-shallow junctions. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2006, 253, 46-49.	1.4	7
125	Evolution of boron-interstitial clusters in preamorphized silicon without the contribution of end-of-range defects. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 154-155, 247-251.	3.5	7
126	Role of ion mass on damage accumulation during ion implantation in Ge. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 118-121.	1.8	7



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127	Chalcogen-hyperdoped germanium for short-wavelength infrared photodetection. AIP Advances, 2020, 10, .	1.3	7
128	Clustering of ultra-low-energy implanted boron in silicon during activation annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 219-223.	3.5	6
129	Dissolution kinetics of B clusters in crystalline Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 32-38.	3.5	6
130	Interaction between implanted fluorine atoms and point defects in preamorphized silicon. Nuclear Instruments & Methods in Physics Research B, 2005, 230, 220-224.	1.4	6
131	Fluorine-enhanced boron diffusion in germanium-preamorphized silicon. Journal of Applied Physics, 2005, 98, 073521.	2.5	6
132	Carrier mobility and strain effect in heavily doped p-type Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 220-223.	3.5	6
133	Investigation of fluorine three-dimensional redistribution during solid-phase-epitaxial "regrowth of amorphous Si. Applied Physics Letters, 2012, 101, 103113.	3.3	6
134	Improved retention of phosphorus donors in germanium using a non-amorphizing fluorine co-implantation technique. Journal of Applied Physics, 2018, 123, 161524.	2.5	6
135	Indiffusion of oxygen in germanium induced by pulsed laser melting. Materials Science in Semiconductor Processing, 2018, 88, 93-96.	4.0	6
136	Lattice curvature of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs [001] graded buffer layers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 3578-3581.	2.1	5
137	A TEM and SEM-cathodoluminescence study of oval defects in graded InGaAs/GaAs buffer layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 120-124.	3.5	5
138	Modeling of Self-Interstitial Diffusion in Implanted Molecular Beam Epitaxy Silicon. Materials Research Society Symposia Proceedings, 2002, 717, 1.	0.1	5
139	Dopant behaviour and damage annealing in silicon implanted with 1 keV arsenic. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 271-275.	1.4	5
140	Radiation enhanced diffusion of B in crystalline Ge. Thin Solid Films, 2010, 518, 2386-2389.	1.8	5
141	Erbium "oxygen interactions in crystalline silicon. Semiconductor Science and Technology, 2011, 26, 055002.	2.0	5
142	Non-Conventional Characterization of Electrically Active Dopant Profiles in Al-Implanted Ge by Depth-Resolved Micro-Raman Spectroscopy. Applied Physics Express, 2013, 6, 042404.	2.4	5
143	p-type doping of Ge by Al ion implantation and pulsed laser melting. Applied Surface Science, 2020, 509, 145230.	6.1	5
144	New method for the production of thin and stable, segmented n <sup>+</sup> +p <sup>+</sup> contacts in HPGe detectors. European Physical Journal A, 2021, 57, 1.	2.5	5

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145	Plasma processing: a novel method to reduce the transient enhanced diffusion of boron implanted in silicon. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 18-22.	1.4	4
146	Two-dimensional interstitial diffusion in silicon monitored by scanning capacitance microscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 148-151.	3.5	4
147	Suppression of Boron Diffusion by Fluorine Implantation in Pre-amorphized Silicon. Materials Research Society Symposia Proceedings, 2004, 810, 19.	0.1	4
148	Electrical activation and lattice location of B and Ga impurities implanted in Si. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 727-731.	1.4	4
149	A non-destructive approach for doping profiles characterization by micro-Raman spectroscopy: the case of B-implanted Ge. Journal of Raman Spectroscopy, 2014, 45, 197-201.	2.5	4
150	N-type doping of Ge by P spin on dopant and pulsed laser melting. Semiconductor Science and Technology, 2020, 35, 065002.	2.0	4
151	Thermal Stability and Substitutional Carbon Incorporation far above Solid-Solubility in Si <sub>1-x</sub> C <sub>x</sub> and Si <sub>1-x-y</sub> Ge <sub>x</sub> C <sub>y</sub> Layers Grown by Chemical Vapor Deposition using Disilane. Materials Research Society Symposia Proceedings, 2002, 717, 1.	0.1	4
152	Dissolution of donor-vacancy clusters in heavily doped n-type germanium. New Journal of Physics, 2020, 22, 123036.	2.9	4
153	Static and dynamic screening of the polarization fields in nitride nanostructures: a theoretical and experimental study. Physica B: Condensed Matter, 2002, 314, 35-38.	2.7	3
154	Point defect engineering in pre-amorphized silicon enriched with fluorine. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 94-99.	1.4	3
155	Fluorine incorporation in pre-amorphized silicon. Journal of Vacuum Science & Technology B, 2006, 24, 433.	1.3	3
156	Experimental investigations of boron diffusion mechanisms in crystalline and amorphous silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 240-246.	3.5	3
157	He implantation to control B diffusion in crystalline and pre-amorphized Si. Journal of Vacuum Science & Technology B, 2008, 26, 386.	1.3	3
158	Comment on "Diffusion of n-type dopants in germanium" [Appl. Phys. Rev.1, 011301 (2014)]. Applied Physics Reviews, 2015, 2, 036101.	11.3	3
159	Enhanced recrystallization and dopant activation of P <sup>+</sup> ion-implanted super-thin Ge layers by RF hydrogen plasma treatment. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	3
160	Phosphorus precursors reactivity versus hydrogenated Ge surface: towards a reliable self-limited monolayer doping. Applied Surface Science, 2021, 541, 148532.	6.1	3
161	Laser-induced activation of Mg-doped GaN: quantitative characterization and analysis. Journal Physics D: Applied Physics, 2022, 55, 185104.	2.8	3
162	Ex-situ n-type heavy doping of Ge <sub>1-x</sub> Sn <sub>x</sub> epilayers by surface Sb deposition and pulsed laser melting. Applied Surface Science, 2022, 600, 154112.	6.1	3

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163	Plasma processing of the silicon surface: A novel method to reduce transient enhanced diffusion of boron. <i>Journal of Applied Physics</i> , 1998, 84, 6628-6635.	2.5	2
164	Diffusion and clustering of supersaturated carbon in SiGeC layers under oxidation. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2002, 186, 212-217.	1.4	2
165	New insight on the interaction and diffusion properties of ion beam injected self-interstitials in crystalline silicon. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2003, 206, 922-926.	1.4	2
166	Boron-interstitial clusters in crystalline silicon: stoichiometry and strain. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 88-91.	3.5	2
167	Effect of Self-Interstitials " Nanovoids Interaction on Two-Dimensional Diffusion and Activation of Implanted B in Si. <i>Solid State Phenomena</i> , 2005, 108-109, 395-400.	0.3	2
168	Fluorine incorporation during Si solid phase epitaxy. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2006, 242, 614-616.	1.4	2
169	Lattice strain of B " B pairs formed by He irradiation in crystalline Si <sub>1-x</sub> B <sub>x</sub> /Si. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2006, 253, 55-58.	1.4	2
170	Thermal evolution of small N-D complexes in deuterated dilute nitrides revealed by in-situ high resolution X-ray diffraction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 2766-2771.	1.8	2
171	In situ thermal evolution of B " B pairs in crystalline Si: a spectroscopic high resolution x-ray diffraction study. <i>Journal of Physics Condensed Matter</i> , 2008, 20, 175215.	1.8	2
172	Optical components in harsh space environment. , 2016, , .		2
173	Formation of F <sub>6</sub> V <sub>2</sub> complexes in F-implanted Ge determined by x-ray absorption near edge structure spectroscopy. <i>Materials Science in Semiconductor Processing</i> , 2017, 62, 205-208.	4.0	2
174	Ex-situ doping of epitaxially grown Ge on Si by ion-implantation and pulsed laser melting. <i>Applied Surface Science</i> , 2020, 509, 145277.	6.1	2
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